

IMPROVED MEMORY DEVICE FOR CONTROLLING PROGRAMMING SETUP TIME

ABSTRACT

[0030] An improved memory device and the method for programming the same are disclosed. The memory device includes at least one memory block requiring a word line pre-charge time to be long enough to program one or more selected memory cells. A monitoring circuit is added for detecting one or more word lines to reach a predetermined threshold voltage to enable a predetermined high voltage to be supplied to one or more latches of the memory cells.